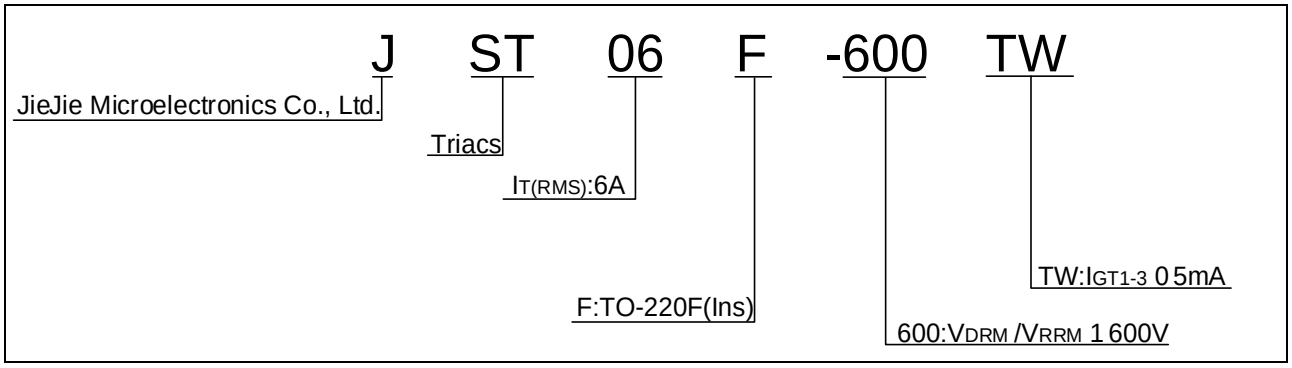
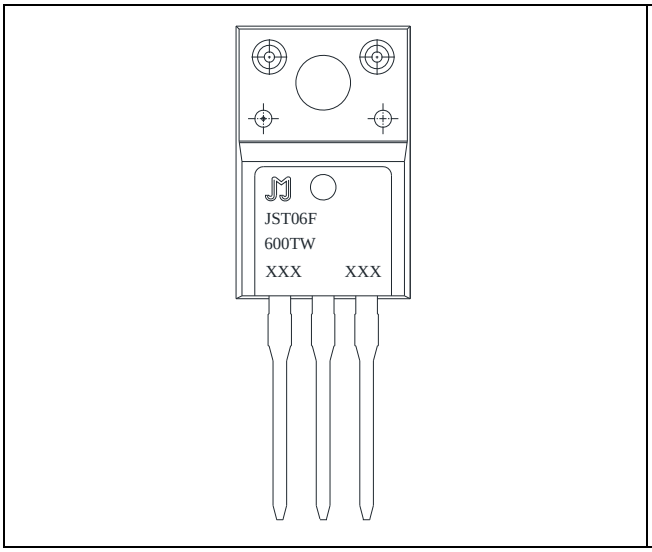
Peak gate current (t_p=20μs , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	10	mA
				15	
I_H	I_T =100mA		MAX.	10	mA
dV/dt	V_D=400V Gate Open T_j =125		MIN.	150	V/μs
(dI/dt)c	(dV/dt)c=10V/μs, T_j=125		MIN.	0.5	A/ms
t_{on}	I_G=10mA I_A=200mA I_R=20mA T_j=25		TYP.	2	μs
t_{off}				20	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =8.5A t_p=380μs	T_j=25	1 .5	V
V_{TO}	Threshold voltage	T_j=125	0.82	V
R_D	Dynamic resistance	T_j=125	57	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0 .2	mA


J
ST
06
F
-600
TW
JieJie Microelectronics Co., Ltd.
Triacs
IT(RMS):6A
F:TO-220F(Ins)
600:VDRM /VRRM 1 600V
TW:IGT1-3 0 5mA


JST06F
600TW
XXX XXX

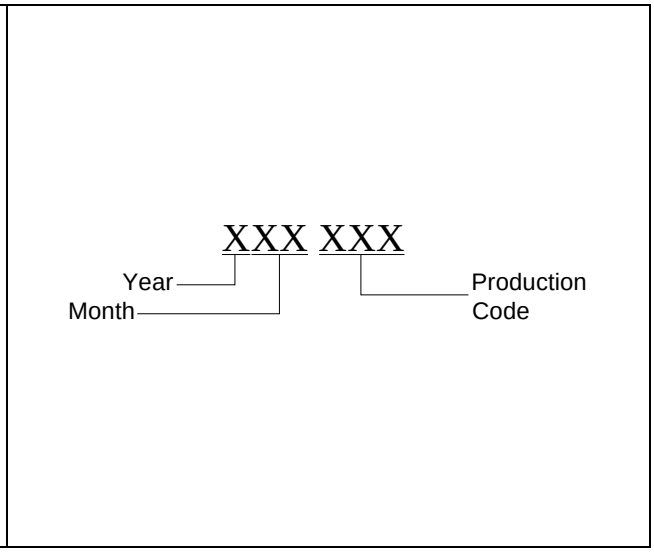

XXX XXX
Year
Month
Production
Code

FIG.1: Maximum power dissipation versus RMS on-state current

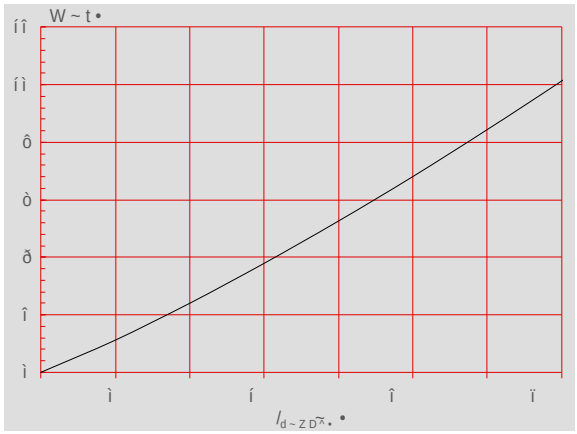


FIG.2: RMS on-state current versus case temperature

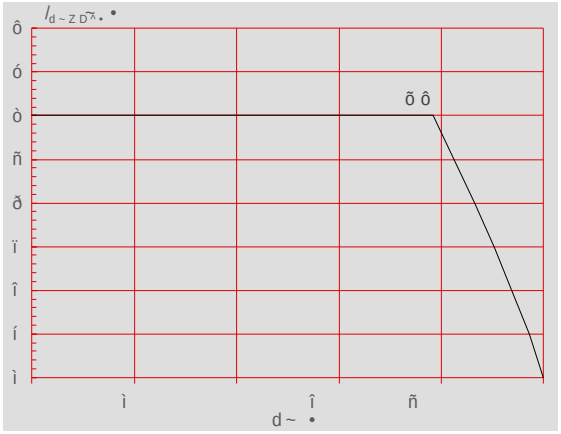


FIG.3: Surge peak on-state current versus number of cycles

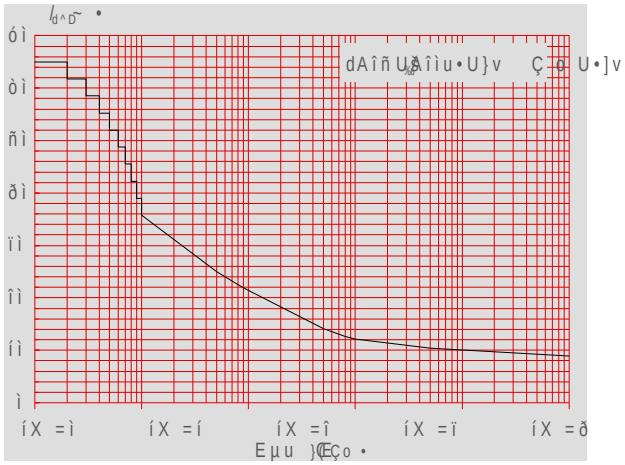


FIG.4: On-state characteristics

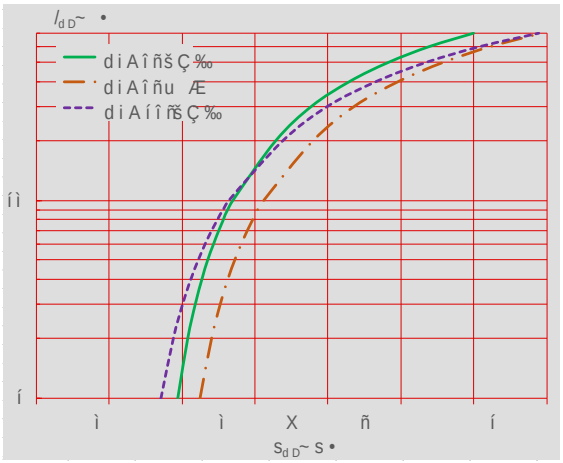


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/µs)

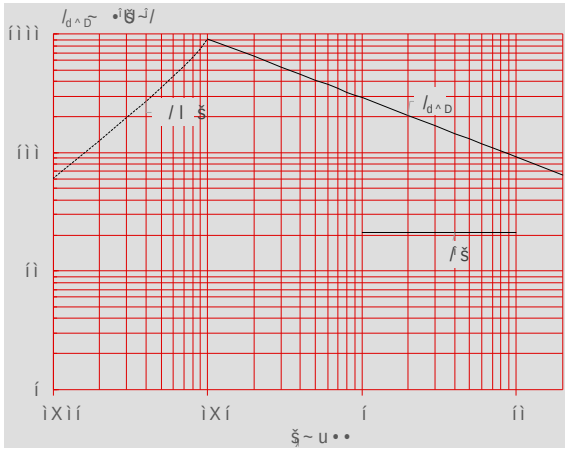


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode

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